

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ Low threshold voltage
- ☒ Source Down
- ☒ ESD protected

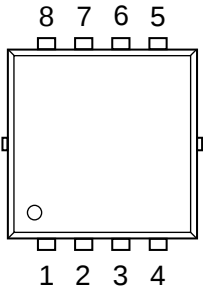
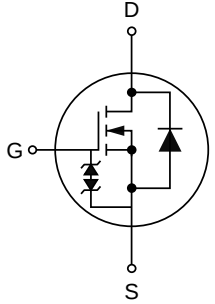
1.2 Applications

- ☒ Motor drivers
- ☒ DC/DC Converter

1.3 Quick reference

- ☒ $BV \geq 16\text{ V}$
- ☒ $R_{DS(ON)} \leq 0.8\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- ☒ $P_{tot} \leq 58\text{ W}$
- ☒ $R_{DS(ON)} \leq 0.9\text{ m}\Omega @ V_{GS} = 2.5\text{ V}$
- ☒ $I_D \leq 100\text{ A}$
- ☒ $R_{DS(ON)} \leq 1.1\text{ m}\Omega @ V_{GS} = 1.8\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1, 2, 3	Source(S)	 Top View PDFN3.3x3.3-8L	
4	Gate(G)		
5, 6, 7, 8	Drain(D)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	-	16	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 10	V
I_D^*	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	100	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	58	A
$I_{DM}^{*,**,***}$	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	144	A
P_{tot}^*	Total Power Dissipation	$T_C=25^{\circ}\text{C}$	-	58	W
T_{stg}	Storage Temperature		-55	150	$^{\circ}\text{C}$
T_J	Junction Temperature		-	150	$^{\circ}\text{C}$
I_S	Diode Forward Current	$T_C=25^{\circ}\text{C}$	-	100	A
E_{AS}^*	Single Pulsed Avalanche Energy	$V_{DD}=20\text{ V}, L=1.0\text{ mH}$	-	388	mJ
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		-	60	$^{\circ}\text{C/W}$
$R_{\theta JC}^*$	Thermal Resistance-Junction to Case		-	6.8	$^{\circ}\text{C/W}$

Notes:

- * Surface Mounted on 1 in² pad area, $t \leq 10\text{ sec}$
- ** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ3308Q	3308 YWWXXX YWW: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ3308Q	PDFN-3.3x3.3-8L	-	-	5000	

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	16	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	0.5	-	1.0	V
I _{DSS}	Drain Leakage Current	V _{DS} =16 V, V _{GS} =0 V	-	-	1	uA
I _{GSS}	Gate Leakage Current	V _{GS} =±10 V, V _{DS} =0 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =4.5 V, I _{DS} =20 A	-	0.7	0.8	mΩ
		V _{GS} =2.5 V, I _{DS} =15 A	-	0.9	1.0	
		V _{GS} =1.8 V, I _{DS} =15 A	-	1.0	1.1	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =10 A, V _{GS} =0 V	-	-	1.1	V
t _{rr}	Reverse Recovery Time	I _{DS} =10 A, dI _{SD} /dt=100 A/μs	-	37	-	ns
Q _{rr}	Reverse Recovery Charge		-	27	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =10 V Frequency=1 MHz	-	3364	-	pF
C _{oss}	Output Capacitance		-	536	-	
C _{rss}	Reverse Transfer Capacitance		-	462	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =10 V, V _{GEN} =10 V, R _G =3.9 Ω, R _L =1 Ω, I _{DS} =10 A	-	8.3	-	ns
t _r	Turn-on Rise Time		-	41	-	
t _{d(off)}	Turn-off Delay Time		-	99	-	
t _f	Turn-off Fall Time		-	51	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{GS} =4.5 V, V _{DS} =10 V, I _{DS} =10 A	-	41	-	nC
Q _{gs}	Gate-Source Charge		-	9.5	-	
Q _{gd}	Gate-Drain Charge		-	12	-	

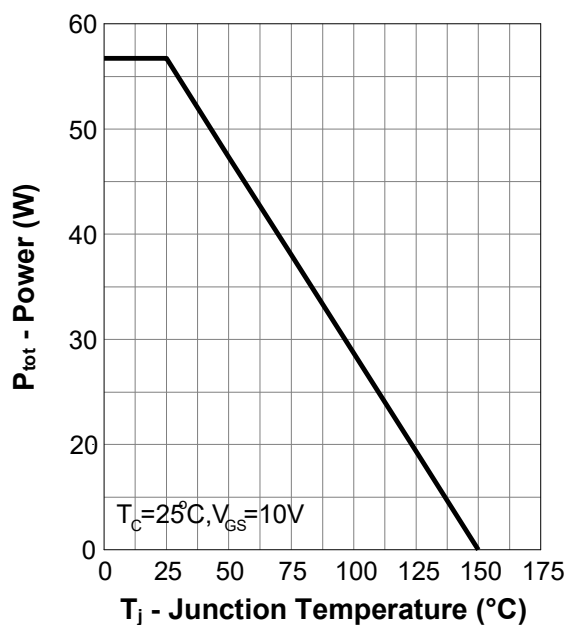
Notes:

a: Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%

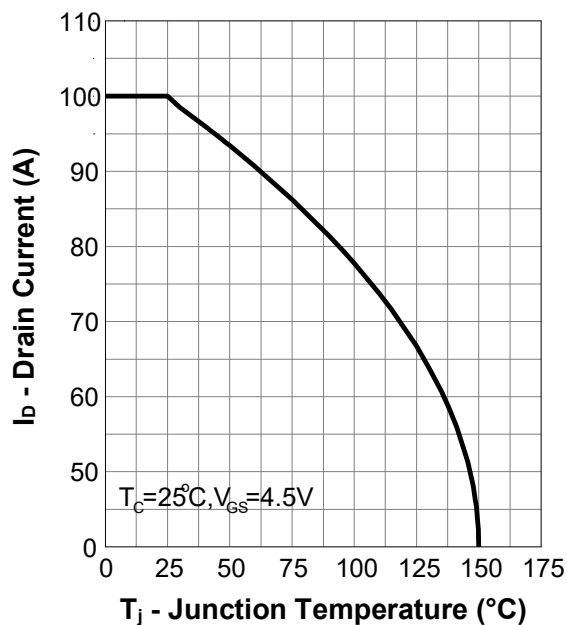
b: Guaranteed by design, not subject to production testing

7. Typical Characteristics

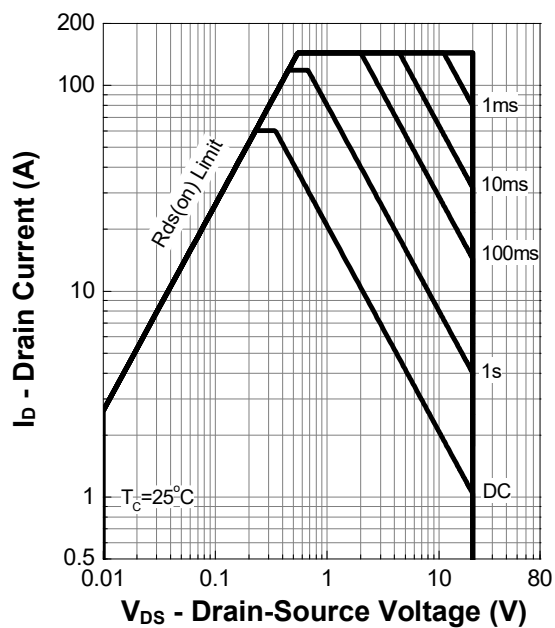
Power Capability



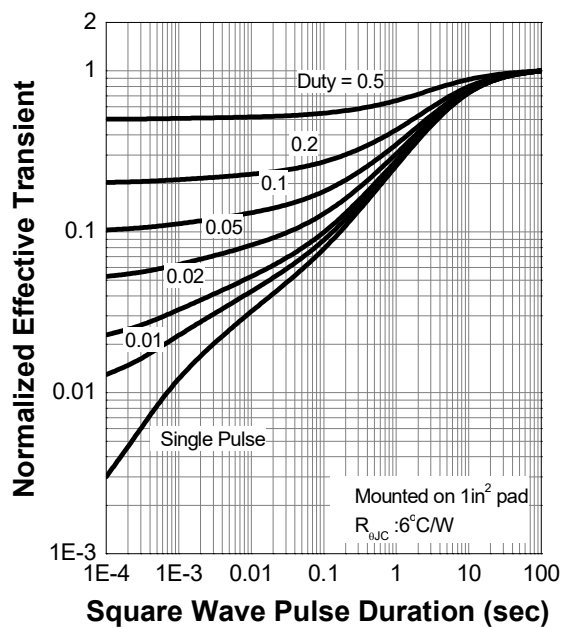
Current Capability



Safe Operation Area

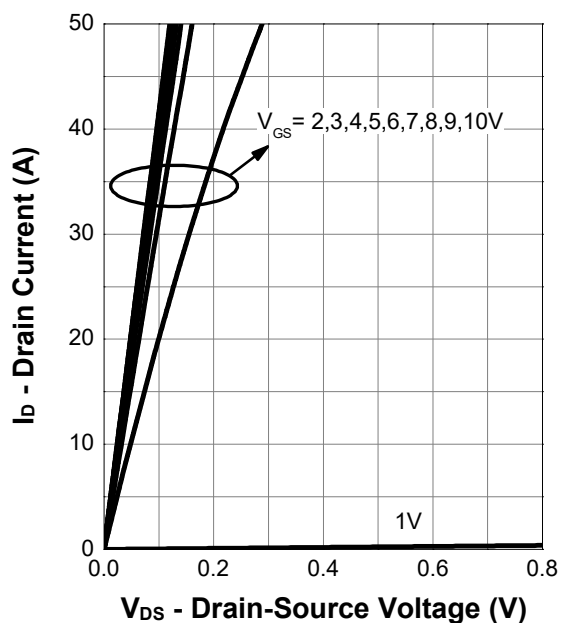


Transient Thermal Impedance

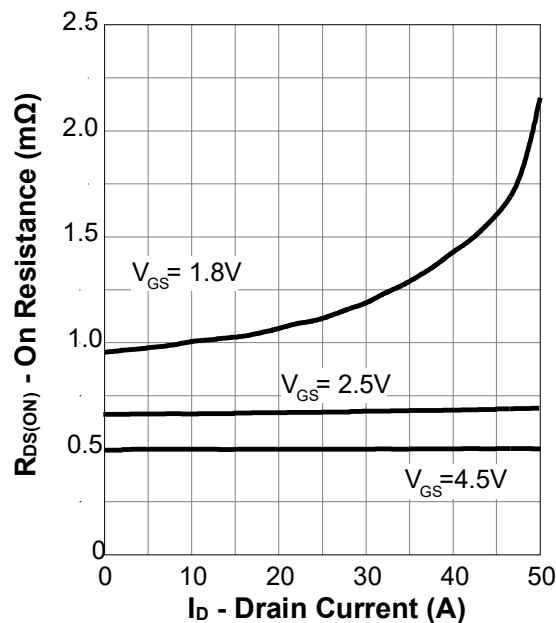


7. Typical Characteristics (cont.)

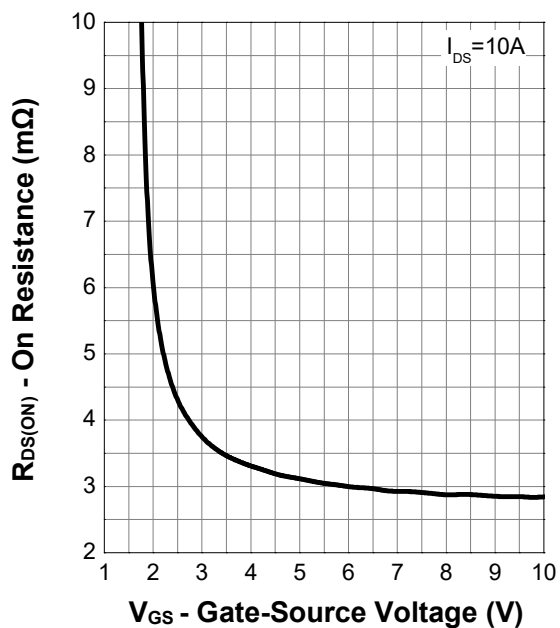
Output Characteristics



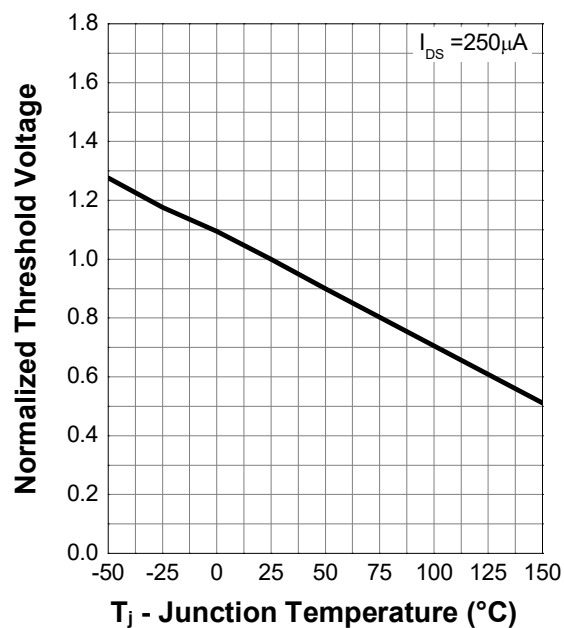
On Resistance



Transfer Characteristics

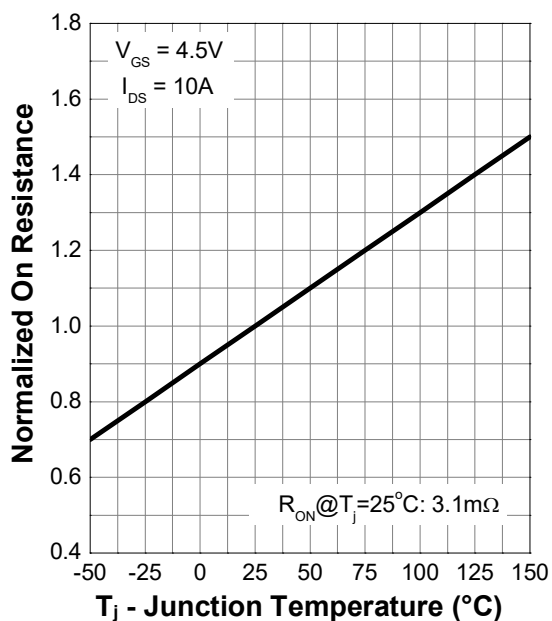


Normalized Threshold Voltage

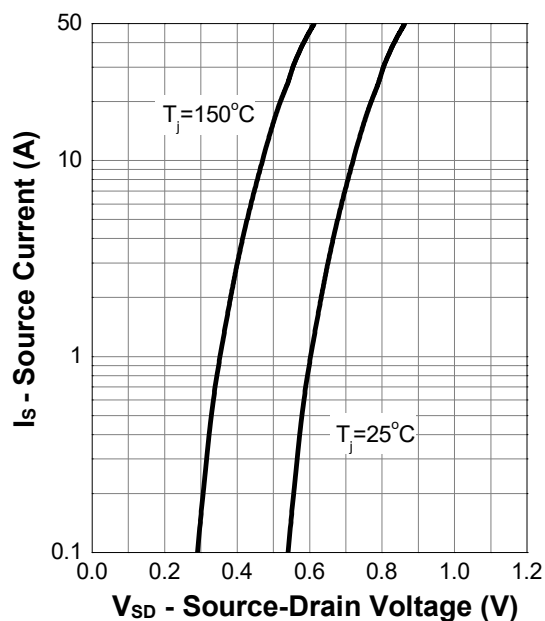


7. Typical Characteristics (cont.)

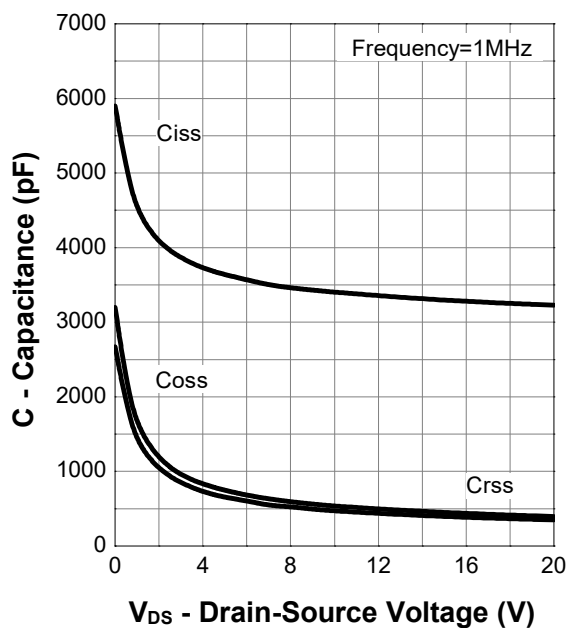
Normalized On Resistance



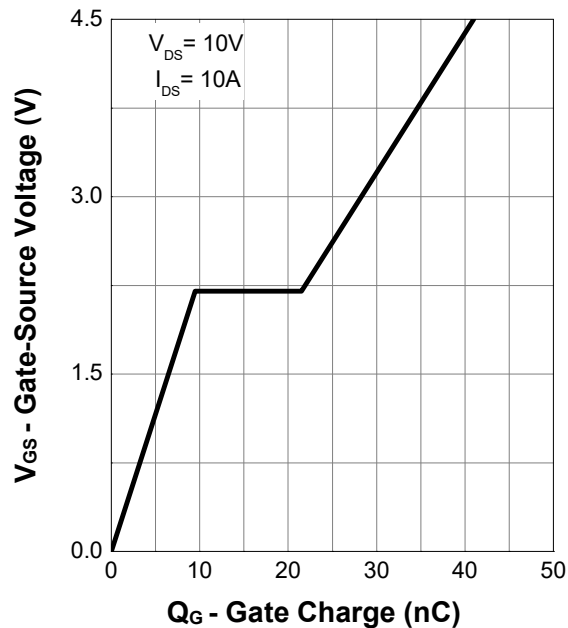
Diode Forward Current



Capacitance

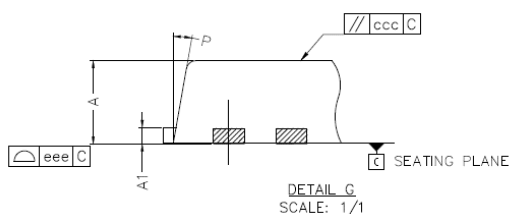
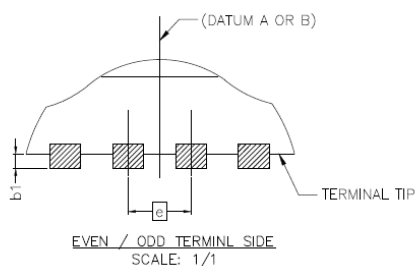
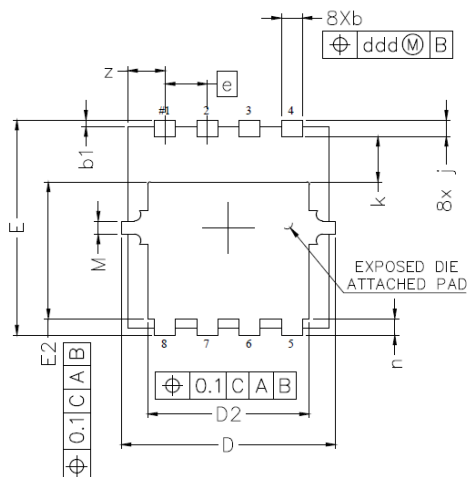
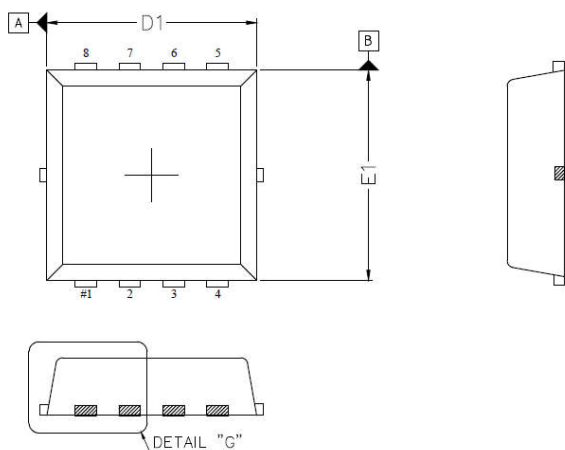


Gate Charge



8. Package Dimensions

PDFN3.3×3.3-8L Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.70	0.90
A1	0.12	0.22
b	0.27	0.37
b1	0.05	0.15
D	3.00	3.60
D1	3.00	3.20
D2	2.29	2.69
E	3.00	3.60
E1	3.00	3.20
E2	2.00	2.20
e	0.60	0.70
j	0.15	0.35
k	0.60	0.80
n	0.15	0.35
M	0.20	
P	9°	11°
z	0.58	
ccc	0.10	
ddd	0.05	
eee	0.05	